

# GSE050AB1N1F

## ESD Protection Diode

### Product Description

It is designed to protect sensitive electronics from damage due to electrostatic discharge (ESD) and other transient events.

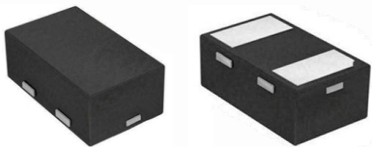

### Features

- Operating Voltage: 5V.
- Bidirectional Configurations
- IEC61000-4-2(ESD)  $\pm 30\text{kV}$  (Air)
- IEC61000-4-2(ESD)  $\pm 30\text{kV}$  (Contact)
- IEC61000-4-4(EFT) 40A (5/50ns)
- IEC61000-4-5(Lighting) 8A (8/20 $\mu\text{s}$ )

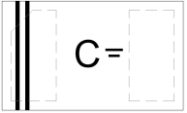
### Mechanical Data

- DFN1006-2L Package
- RoHS Compliant and Halogen Free

### Package and Pin Assignment

DFN1006-2L	Equivalent Circuit
	

## Ordering and Marking Information

GS P/N	Package	Marking	Quantity / Reel
GSE050AB1N1F	DFN1006-2L	C =	10,000PCS
<b>GSE050AB1N1F</b>			
- <b>Product Code:</b> GSE050AB1	- <b>Package Code:</b> N1 for DFN1006-2L	- <b>Green Level:</b> F for RoHS Compliant and Halogen Free	
<b>Marking Information</b>			
	- <b>Product Code:</b> C =		

## Absolute Maximum Ratings (T<sub>A</sub>=25°C unless otherwise specified)

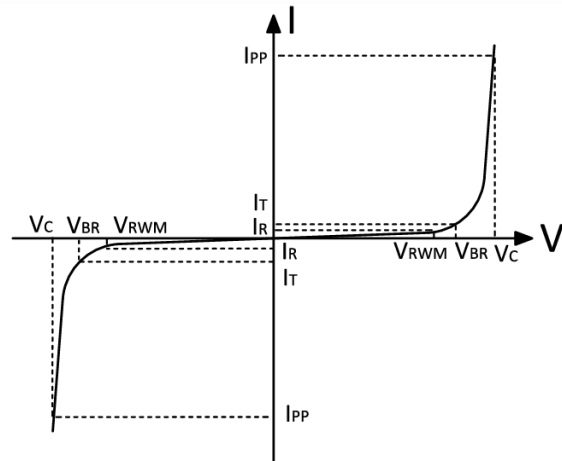
Symbol	Parameter	Value	Unit
P <sub>PP</sub>	Peak Pulse Power (t <sub>p</sub> =8/20μs)	110	W
I <sub>PP</sub>	Peak Pulse Current (t <sub>p</sub> =8/20μs)	8	A
V <sub>ESD</sub>	ESD Per IEC61000-4-2 (Air)	±30	KV
	ESD Per IEC61000-4-2 (Contact)	±30	KV
T <sub>J</sub>	Operating Junction Temperature Range	-55 to +150	°C
T <sub>STG</sub>	Storage Temperature Range	-55 to +150	°C
T <sub>L</sub>	Lead Soldering Temperature (10s)	260	°C

## Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise specified)

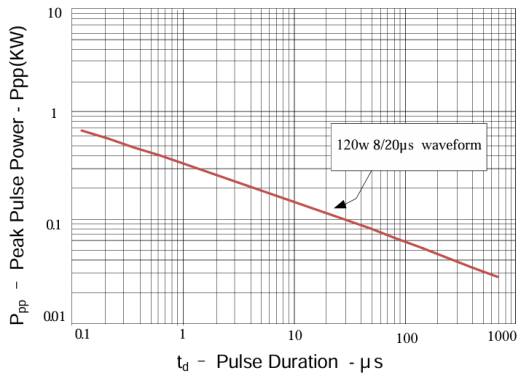
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V <sub>RWM</sub>	Reverse Working Voltage	-			5	V
V <sub>BR</sub>	Reverse Breakdown Voltage	I <sub>T</sub> = 1mA	6.0			V
I <sub>R</sub>	Reverse Leakage Current	V <sub>RWM</sub> =5V			0.5	μA
V <sub>C</sub>	Clamping Voltage	I <sub>PP</sub> =8A (8/20μs)		10	14	V
C <sub>J</sub>	Junction Capacitance	V <sub>R</sub> =0V, f=1MHz		18	23	pF

## Electrical Parameters

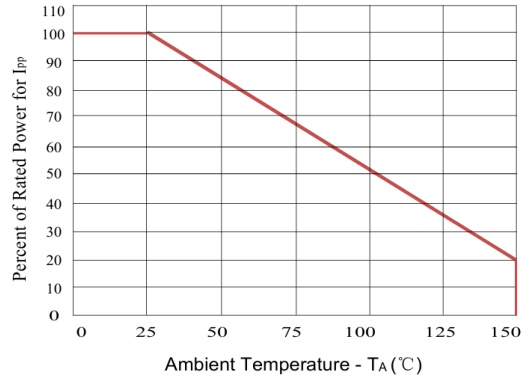
Symbol	Parameter
I <sub>PP</sub>	Reverse Peak Pulse Current
V <sub>C</sub>	Clamping Voltage @ I <sub>PP</sub>
V <sub>RWM</sub>	Reverse Working Voltage
I <sub>R</sub>	Reverse Leakage Current @ V <sub>RWM</sub>
V <sub>BR</sub>	Breakdown Voltage @ I <sub>T</sub>
I <sub>T</sub>	Test Current



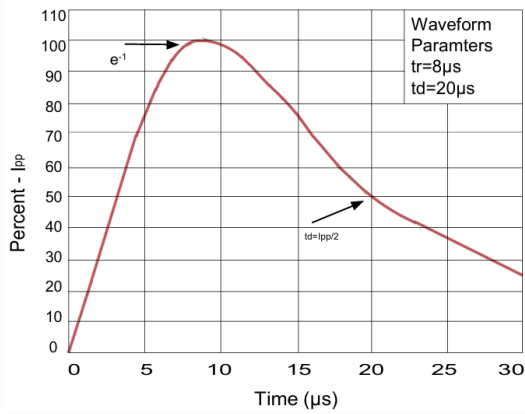
**Typical Characteristics** ( $T_A=25^\circ\text{C}$  unless otherwise specified)



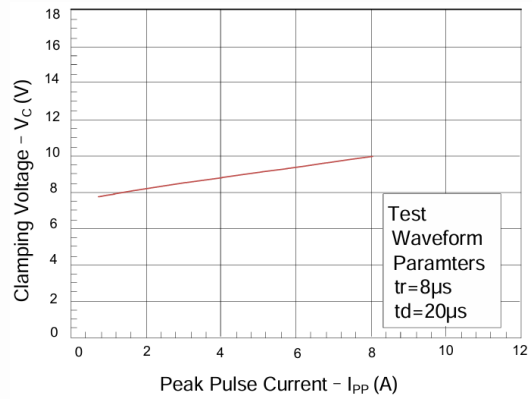
**FIG 1. Peak Pulse Power vs. Pulse Time**



**FIG 2. Power Derating Curve**



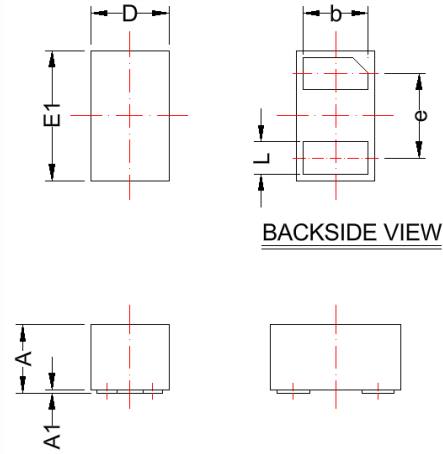
**FIG 3. 8/20μs Pulse Waveform**



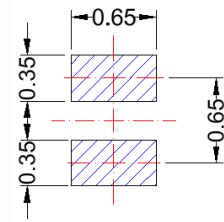
**FIG 4. Clamping Voltage vs. Ipp**

# DFN1006-2L

## Package Dimension



## Recommended Land Pattern



Unit:mm

Dimensions				
Symbol	Millimeters		Inches	
	MIN	MAX	MIN	MAX
A	0.45	0.60	0.018	0.024
A1	0.00	0.05	0.000	0.002
b	0.45	0.55	0.018	0.022
D	0.55	0.65	0.022	0.026
E1	0.95	1.05	0.037	0.041
e	0.65 BSC		0.026 BSC	
L	0.20	0.30	0.008	0.012





**NOTE:**



Dimensions are exclusive of Burrs, Mold Flash & Tie Bar extrusions.

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